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Giant red shift and enhancement of resonant light confinement in planar array of dielectric bars

Vyacheslav V Khardikov[1,2], **Ekaterina O Iarko**[1] **and Sergey L Prosvirnin**[1,2]

[1] Institute of Radio Astronomy of National Academy of Sciences of Ukraine, Kharkiv 61002, Ukraine
[2] Karazin Kharkiv National University, Kharkiv 61077, Ukraine

E-mail: `khardikov@univer.kharkov.ua`, `yarkokatya@rian.kharkov.ua` and `prosvirn@rian.kharkov.ua`

Abstract. Results of research of resonant phenomena in planar periodic structures consisted of dielectric elements are presented. A problem of plane wave diffraction by a structure which a periodic cell is composed of two dielectric bars with different lengths has been solved. For the first time an existence of high Q-factor trapped mode resonances are revealed in these structures. The main difference of studied structure in contrast to the planar structure with a single dielectric bar in the unit cell is appearing of a great red shift of a trapped mode resonant wavelength. The red shift is caused by strong coupling of electromagnetic fields in neighbor dielectric bar resonators. This property is very attractive to design resonant periodic planar structures by using moderate refractive index materials like semiconductors within their transparency window. In the near infrared band, the trapped mode resonances of periodic planar structure with bars made of germanium have been studied. It is shown that decreasing of structure asymmetry degree results in increasing of both red shift and Q-factor of resonance.

Keywords: Trapped mode, Fano resonance, planar dielectric array, germanium periodic structure, light diffraction, infrared wave diffraction.

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1. Introduction

Planar double-periodic structures are widely used in various types of devices in microwave, terahertz and optical wavelengths. They form the basis of classical frequency and polarization selective surfaces [1], high-impedance coatings [2] and such impressive modern subject as metamaterials i.e. artificial materials engineered to have properties which are not found in natural media. For instance, one of the best known exotic properties is a negative refraction index [3] required in particular for transformation optics in order to design electromagnetically invisible cloaks [4]. Some planar metamaterials as so-called fish-scale resonant meta-layers [5] manifest an unusual asymmetric transmission [6, 7] and light reflection that does not change the phase of the incident wave [8]. Designing metamaterials for optical and infrared range is relevant problem for numerous very promising photonic applications.

Usually metamaterials and meta-layers assigned for visible and infrared wavelength ranges are designed on the basis of periodic arrays of complex shaped metallic wire particles placed on a dielectric substrate. The complex shape of metallic elements efforts an opportunity to achieve a resonant light reflection and transmission in periodic structures without diffraction orders which appear in the host space and substrate. At the normal wave incidence such regime of interaction between light and structure occurs in the case when the array period is smaller than light wavelength in the substrate and host medium.

Unfortunately Q-factor of the resonances excited in such structures is very small because a high level of radiation losses and huge energy dissipation which inherent to metals in the infrared and optical ranges. On the other hand there are numerous important applications of meta-layers which require a strong confinement of electromagnetic field inside the periodic structure. First of all they are related to control of the reflection and transmission of light with light which is realized by involving gain medium [9] or nonlinear elements [10] in the structure.

A value of the radiation losses depends on the degree of electromagnetic coupling between induced currents in metallic elements and fields of plane waves in free space and substrate. Not long ago it was shown theoretically [11, 12, 13] and then confirmed experimentally [14] that there are specially engineered kinds of double-periodic open planar structures which have a different peculiar type of high-Q resonance in microwave range. This type of resonances is a result of an excitation of antisymmetric current mode in metallic particles placed inside periodic cell of the array. The antisymmetric current mode may exist in arrays composed of some complex-shaped metallic elements arranged in array which periodic cell consists of at least two metallic elements. Their specific character comes from anti-phased currents in metallic elements of a periodic cell. Such current mode has a very small electromagnetic coupling with plane waves in free space and substrate. Moreover the coupling depends strongly on the symmetry degree of a structure. For example, this coupling may be equal to zero in fully symmetric structure. Thus antisymmetric current mode may exists in such structure but they cannot be excited by the incident plane wave. Such resonances are known as "trapped-mode" resonances.

For almost symmetrical structure the radiation losses of trapped-mode resonances may be decreased up to zero. Evidently, the Q-factor of trapped mode resonance of a hypothetic non-dissipative structure may reach an infinitely large value. It is a main feature of trapped mode resonances which distinguishes them from ordinary dimensional resonances, i.e. resonances which appears in planar periodic structures with single dielectric element inside periodic cell. To excite trapped-mode resonance in the structure it is required to introduce some asymmetry of the metallic elements caused by difference in their shape or sizes.

Another very important feature of structures which supported the trapped mode resonances is an existence of a periodic cell symmetry axis. To excite trapped mode resonances in a double-periodic planar structure with two asymmetric metallic elements in a periodic cell, the incident plane wave must be polarized orthogonally to the periodic cell symmetry axis.

Unique properties of trapped mode resonances attract rapt attention to design the planar periodic structures for optical and infrared wavelengths. Now existence conditions and properties of trapped mode resonances in periodic metal-dielectric planar structures developed for near infrared range have been studied in details [15, 16]. The trapped mode reflection and transmission resonances have a much higher Q-factor in comparison with that ones of ordinary dimensional resonances. However metals have a strong dispersion in this wavelength range and, as a result, the dissipative losses of metals are extremely large. Since the trapped mode resonances are accompanied with high amplitude of currents in metallic elements, the essential dissipative losses are observed in the structure. As the structure asymmetry decreases the radiation losses decreases too, but at the same time, it results in growing current amplitudes and increasing the dissipative losses. Thus in the near infrared range, the Q-factor of trapped mode resonance essentially exceeds that for ordinary dimensional resonance but anyway its value is not more than several tens.

Since intrinsic dissipative losses which exist in plasmonic metallic structures are unavoidable, the idea of their compensation by using parametric processes and gain media was proposed [17, 18]. Experimental demonstrations of compensation of absorption losses in metallic trapped mode metamaterial by using optically pumped semiconductor quantum dots were presented in [19, 20]. Observed narrowing of the quantum dots photoluminescence spectrum is an evidence of Q-factor increasing in the pumped structure.

Nevertheless using metallic plasmonic structures is not only single possible way to develop thin planar structures for strong enhancement of confinement resonant field and getting magnetic response. An evident way to produce low-dissipative structures, which have the similar electromagnetic properties, lies in using solely dielectric elements for designing double-periodic structures supported the trapped mode resonances.

Recently it was shown by simulation in microwaves that left-handed media may be constructed on the basis of cubic high dielectric resonators [21] or dielectric rings and rods [22] putted together.

However the origin of the resonance in metal-dielectric and purely dielectric structures has a principal difference. Resonant phenomena in metal-dielectric structures are the result of the plasmon-polariton excitation, which are surface wave propagating along the metal-dielectric boundaries. It can be considered as current which flow in the metallic elements and repeat their intricate shape. Thus the complex shaped metallic elements can be used to provide condition of the resonant light interaction with structures in the range where wavelengths exceed the size of a periodic cell. The resonance is observed if characteristic dimension of metallic elements is approximately equal to integer number of the half plasmon-polariton wavelength.

Elements of dielectric periodic structures are open volume dielectric resonators. It is important that the dimensions of these resonators are under constraint of smallness of the structure periodic cell in comparison with the wavelength. Unfortunately a shape complication of the dielectric elements does not imply increasing resonant wavelength like in the case of metallic elements. Thus we need to study in detail the trapped mode resonance of purely dielectric periodic planar structures.

This paper deals with studying existence conditions and main properties of the near infrared trapped mode resonance in double-periodic planar structure which consists of a pair of resonant dielectric elements in the periodic cell. Let us note that this resonance is quite different from reflection and transmission resonances which are the result of the excitation of surface eigenwaves in the dielectric layer with holes or inclusions.

2. Problem statement and method of solution

Let us consider a dielectric rectangular parallelepiped with square cross section as a constituent element of purely dielectric array. Thus the problem of light diffraction by double-periodic planar array of dielectric parallelepipeds placed on a dielectric substrate with thickness L is considered (see Fig. 1). A periodic cell of the array includes a pair of dielectric parallelepipeds which have different lengths but the same cross sections and materials. The length of longer dielectric element is h_1 and shorter one is h_2 ($h_1 \geq h_2$). Sizes of the square periodic cell are chosen to be $d_x = d_y = 975$ nm. Minimal distance between longer and shorter dielectric elements are chosen to be 195 nm for all two-elements dielectric arrays. The periodic cell is symmetric relatively to line which is parallel to Oy-axis and passing through its centre. The normal incidence of linearly x-polarized plane wave is considered. We study the resonant responses of the array in the near infrared wavelength range from 1000 nm to 3000 nm. The substrate material is assumed to be synthetic fused silica (amorphous silicon dioxide). Its refractive index is approximately 1.44 in the wavelength range [23] under consideration.

It is known [16] that the trapped mode resonances in the array with two metallic elements in the periodic cell are excited in the wavelength band between wavelengths of ordinary dimensional resonances in arrays which consist of the same metallic elements but only one kind and with single such element per the periodic cell. Therefore we may expect that the trapped mode resonance of a dielectric array is formed when each of the dielectric elements has sizes closed to the resonant ones. Thus, to provide a resonant light reflection without forming diffraction orders we chose the dielectric bars having resonant wavelength larger then the structure period. The dielectric bar resonant wavelength depends on its sizes and permittivity. The length of dielectric bar must be less then the size of periodic cell. Besides we will restrict the size of dielectric bar cross section by the following condition $l\sqrt{\varepsilon} < \lambda/2$ where ε is the relative permittivity of dielectric and l is the cross section size. This restriction provides absence of appearing transverse interference resonances along bar cross section. The value of dielectric bar permittivity is also substantially limited by properties of known dielectric materials in infrared wavelength region suitable for dielectric array production. Majority of dielectrics using in microchip technologies have permittivity which is not exceed four. However semiconductors may be used as material of elements of periodic array. Using semiconductors is promising because they have transparency windows in the infrared and optical regions. Permittivity of well-known suitable semiconductors has a value from 11 to 18 and their dielectric loss tangent does not exceed 10^{-3} within transparency windows. For example, germanium transparency window extends from

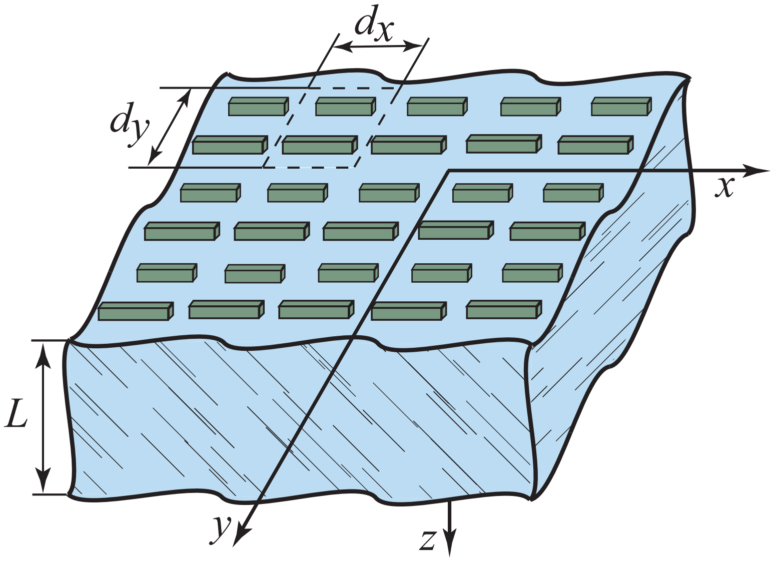


Figure 1. Geometry of double-periodic planar structure with two dielectric bars in a periodic cell.

1600 nm to 2000 nm and its refractive index varies from 4.07 to 4.23 through this window [24]. Taking into account all above mentioned, the size of square cross section of dielectric bars is chosen to be $l = 195$ nm.

To solve the diffraction problems, the numerical method proposed in [25] is used. This method is based on the both mapped PSTD method [26] and transfer matrix theory. In this paper the dispersion of dielectrics does not take into account. Relevancy of such approach is conditioned by two reasons. Firstly, the dispersion of chosen materials is very weak in frequency region being under consideration, secondly, dispersion of the materials does not effect on the conditions and properties of trapped mode resonances. However the materials dispersion may be taken into account without any problems in the context of used method.

3. Trapped mode resonances in arrays consisted of dielectric bars

Let us consider an incident wave reflection from the dielectric array placed on an infinitely thick substrate. We assume that silica is filled all half space $z > 0$ below array to simplify an analysis by excluding interference resonances in the substrate. As it is known and was shown by simulation in [25] the actual finite thickness of substrate results in interference fringes along of wavelength dependences of reflection and transmission coefficients. In actual structures which substrate thickness is approximately 0.5 mm these interference resonances are destroyed because a local heterogeneity of the substrate.

To have data for a comparison, at first, we will consider the trapped mode resonances in a periodic array of metallic parallelepipeds. The analysis of simulation results shows the conditions of trapped mode resonances excitation. The nature of resonant characteristics of arrays with only one metallic bar in periodic cell is evident. It is ordinary plasmon-polariton resonance which is excited under the condition

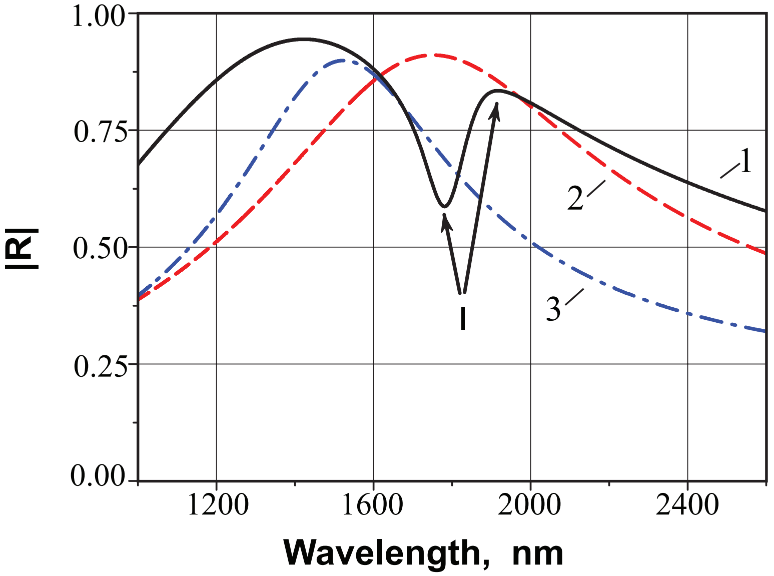


Figure 2. Wavelength dependences of the magnitude of reflection coefficients for double-periodic structures with two gold bars in periodic cell (h_1 = 450 nm and h_2 = 400 nm, line 1) and single gold bar in periodic cell with length 450 nm (line 2) and 400 nm (line 3). Sizes of periodic cell and bar cross section are 500 nm and 50 nm, respectively.

$h = \lambda_p/2$, where h is the length of metallic element and λ_p is the wavelength of plasmon-polariton. The trapped mode resonance of array with two metallic bars in periodic cell occurs due to the excitation of anti-phased plasmon-polaritons in the bar pairs.

For distinctness let us start our study from analysis of trapped mode resonance in an array with two gold bars in the periodic cell. The bars of these pairs have different lengths. The lengths of longer and shorter bars are 450 nm and 400 nm, respectively. Minimal distance between longer and shorter bars equals to 100 nm. The square periodic cell of structure under study has sizes $d_x = d_y = 500$ nm. The array is placed on the silica infinite substrate. Since metals have strong inherent dispersion in the near infrared range we take into account the gold dispersion using the method of additional differential equation and complex-pole model (see, for example [16]).

Wavelength dependence of the magnitude of the reflection coefficient of such array is depicted in Fig. 2 (line 1). Another two lines present the wavelength dependences of reflection coefficient magnitudes of arrays with single gold bar in the periodic cell. Line 2 corresponds to the array which consists of longer bars belonged to the two-element array and line 3 corresponds to the array of shorter ones. The trapped mode resonance of the two-element structure with the pair of gold bars in the periodic cell occurs at the same wavelength band where the reflection resonances of one-element arrays of single bars are observed. Trapped mode resonance has the Fano-shape [27] and it is marked by I in Fig. 2.

Thus we may suppose that the trapped mode resonance of the array of dielectric bars is formed in the wavelength region where one-element arrays of single dielectric bars have ordinary dimensional resonances. The inequality $\lambda_r > n_{sub}d_x$ provides a condition for the resonance in the array of dielectric bars without forming diffraction orders in both free space and the substrate. Here λ_r is the resonant wavelength and n_{sub} is the substrate refractive index. To fulfil the mentioned requirement we assume that the refractive index of dielectric of bars has a value which is exceeded 4.5.

Firstly we consider arrays which are made of hypothetic lossless dielectric with refractive index equals to 5.5. Such choice efforts an opportunity to observe two reflection resonances of one-element arrays of dielectric bars in the wavelength range where spatial diffraction orders are not excited. Wavelength dependences of reflection coefficient magnitudes are shown in Fig. 3 for array of two dielectric bars in the periodic cell (line 1) and for one-element arrays. Lines 2 and 3 correspond to the array of longer dielectric bars and the array of shorter ones, respectively. There are two reflection resonances of the one-element arrays in the considered wavelength range. They are ordinary dimensional resonances which appear in the bars, and, in this case, the bars are considered as dielectric resonators with conditions $h_i \approx \lambda_d/2$ and $h_i \approx 3\lambda_d/2$ $(i = 1, 2)$, where λ_d is the wavelength in the dielectric of bars. This fact was confirmed by calculations and analysis of electric field distributions along the periodic cell and inside the bar of arrays.

When we put together longer and shorter dielectric bars in the periodic cell then additional reflection resonances are arisen which can be seen in Fig. 3 (line 1). Especial interest is stimulated by the additional resonance in long-wave part of the considered wavelength range. It is typical Fano-shape sharp resonance with specific wavelength dependence of reflection coefficient rolled over deep to peak.

Electric field distributions within the periodic cell were drawn and studied for all additional resonances to understand their nature. One of such distributions which is related to the plane $z = l/2$ is shown in Fig. 4 at the wavelength 2208 nm corresponded to the additional resonance with maximum wavelength. As the field has symmetric distribution we present it within only a half of the periodic cell.

One can see that both dielectric bars operate as a half-wavelength dielectric resonator, i.e. maximum of electric field lies close to the center of dielectric bar and field fall down to bar facets (Fig. 4,b). Electric field maxima are originated outside the bar at its ends are resulted by strong change of permittivity. The continuity conditions of normal component of electric field induction are fulfilled on bar ends, i.e. one can write following equality $E_{x-} = \varepsilon E_{x+}$, where E_{x-} and E_{x+} are electric fields in free space and inside the bar, respectively. It is evident that the electric field is not zero on the edges of an open dielectric resonator. Thus the electric field has a value in free space between the bars in ε times more than the field inside the bars. In our case this coefficient is $\varepsilon = 30.25$.

The field distribution manifests that the studied resonance is a trapped mode one since electric field has opposite phases and approximately the same absolute values inside the dielectric bars. Let us notice that E_y component has a maximum value of the same order as the maximum of E_x component and maximum of E_z component has a value more then 100 times less.

The main distinctive feature of the trapped mode resonance of two-element dielectric array is the fact that there is a great red shift of its wavelength relatively to the resonant wavelengths of corresponding one-element arrays (see Fig. 3). Thus a coupling of dielectric bars of two-element periodic array results in extremely large increasing of resonant wavelength contrary to the interaction result in the array of metallic bars (see Fig. 2). This property of purely dielectric trapped-mode arrays is important for possible applications in the promising field of infrared metamaterials.

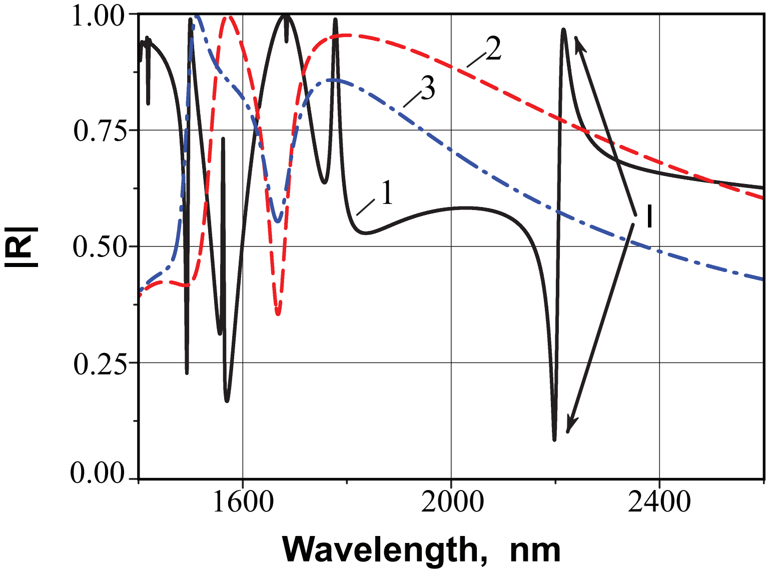


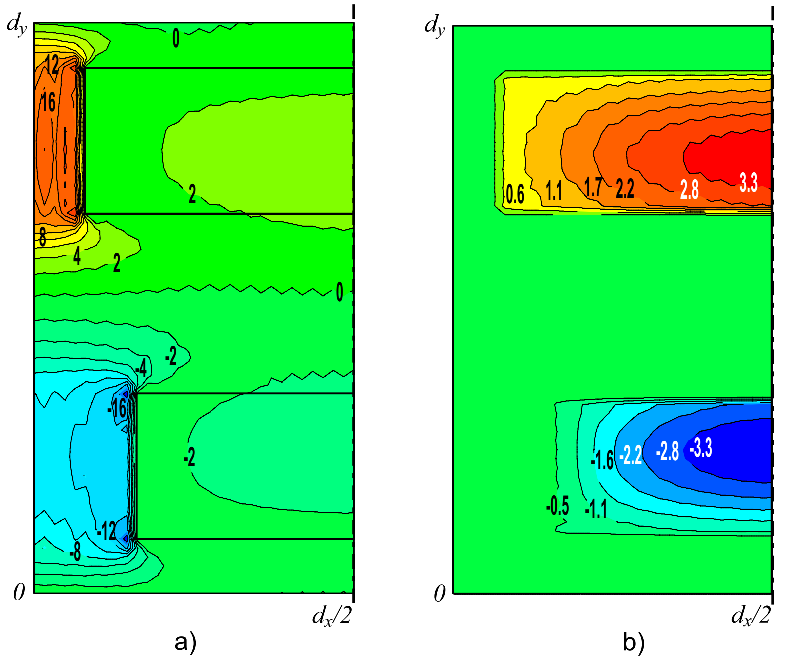
Figure 3. Wavelength dependences of the magnitude of reflection coefficients of arrays made of two dielectric bars in periodic cell ($h_1 = 877$ nm and $h_2 = 780$ nm, line 1) and single dielectric bar which length is 877 nm (line 2) or 780 nm (line 3). Sizes of the periodic cell and the bar cross sections are 975 nm and 195 nm, respectively. The refractive index of the bar dielectric is 5.5. .

First, we can decrease the ratio of array pitch to wavelength to design more homogeneous metamaterials. Second, an increasing of resonant wavelength results in an enhancement of confinement of field intensity because decreasing of radiation losses. It is important for designing nonlinear and active artificial media. Third, this property of dielectric arrays gives us the way to design double-periodic structures sustained the trapped mode resonance using materials with relatively small refractive index, for example, made of semiconductors in the frequency range of their transparency windows.

The research of the field distributions for the rest additional resonances of the studied two-element dielectric array (see Fig. 3) results in the conclusion that they are ordinary dimensional resonances.

Now let us study a more realistic array which consists of germanium bars with the mentioned above sizes. The refractive index of germanium is assumed to be equal to 4.12. Such value of the germanium refractive index corresponds to the wavelength range from 1850 nm to 1950 nm. This range is shaded in Fig. 5 where a wavelength dependence of the reflection coefficient of the array is presented. We observe the trapped mode resonance in this wavelength range.

Fig. 5 illustrates the effect of an array asymmetry being a consequent of a difference of bar lengths on wavelength and Q-factor of trapped mode resonance. It is clear that the trapped mode resonance cannot be excited by normally incident plane wave in symmetrical structure with the same lengths of both bars because zero coupling of asymmetrical mode of bars and plane wave in the free space and substrate (see line 1 in Fig. 5). Decreasing the asymmetry degree which is designated by the value h_1/h_2 results in increasing the red shift of trapped mode resonance and decreasing



a)

b)

Figure 4. A distribution of x-component of an electric field in the plane $z = l/2$ within a periodic cell of the two-element dielectric array. The field distribution is presented in longest resonant wavelength 2208 nm (see Fig. 3). Because electric field values are essentially different inside and outside of the bars, for the sake of convenience, we present the field distribution in whole periodic cell (a) and only inside dielectric bars (b) with different field scales.

wavelength difference between reflection deep and peak, i.e. increasing the trapped mode resonance Q-factor.

To estimate the trapped mode resonance Q-factor let us consider the expression $Q = \lambda_1\lambda_2/(2\lambda_0(\lambda_2 - \lambda_1))$, where λ_1 and λ_2 are wavelengths of deep and peak of the reflection coefficient magnitude, respectively, and λ_0 is the wavelength corresponded to the reflection coefficient value $(|R(\lambda_1)| + |R(\lambda_2)|)/2$. The Q-factors of trapped mode resonances of the structures consisted of germanium bars are 203 and 1080 for the cases of $h_1 = 877$ nm, $h_2 = 780$ nm and $h_1 = 877$ nm, $h_2 = 838$ nm, respectively (see lines 2 and 3 in Fig. 5 for a comparison). Let us note that in the case of the structure consisted of dielectric bars with refractive index 5.5 (see Fig. 3, line 1) the Q-factor of the trapped mode resonance is 127.

It is clear that the semiconductors dissipative losses will strongly effect on the Q-factor of the trapped mode resonance. However in the case when dielectric loss tangent of germanium is not exceed 10^{-3} (this wavelength band is given in Fig. 5 as a shaded area), one can see negligible change of reflection level and a very small widening of the trapped mode resonance which reveals a decreasing the Q-factor (see Fig. 6).

As it was mentioned above, the strong field which is confined in the periodic array in the regime of trapped mode resonance may effectively interact with a substrate made of active or nonlinear materials. In the first case, one can obtain an amplification of reflected or transmitted light. In the case of nonlinear substrate, controlling light with

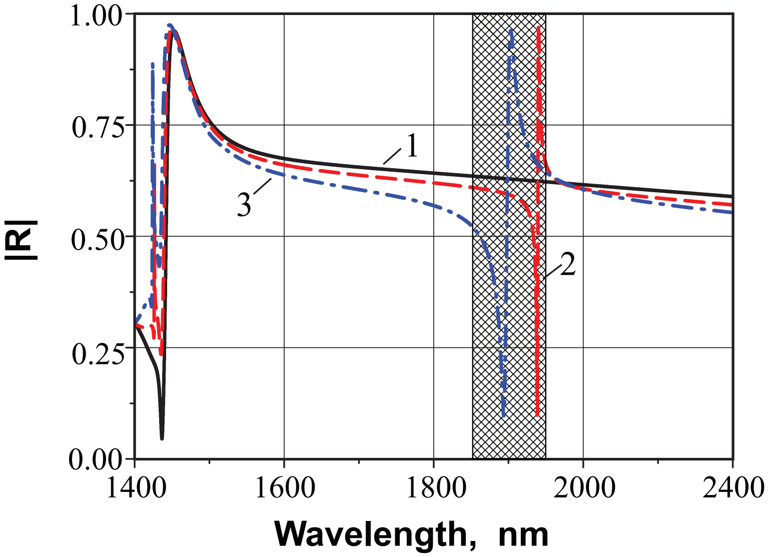


Figure 5. Wavelength dependences of magnitude of reflection coefficient of arrays consist of two germanium bars in periodic cell. The structure sizes are $d_x = d_y = 975$ nm, $l = 195$ nm, $h_1 = 877$ nm. Lines 1, 2 and 3 correspond to $h_2 = 877$ nm, $h_2 = 838$ nm and $h_2 = 780$ nm respectively. Here it is assumed that the refractive index of germanium is 4.12 and dissipative losses are negligible small.

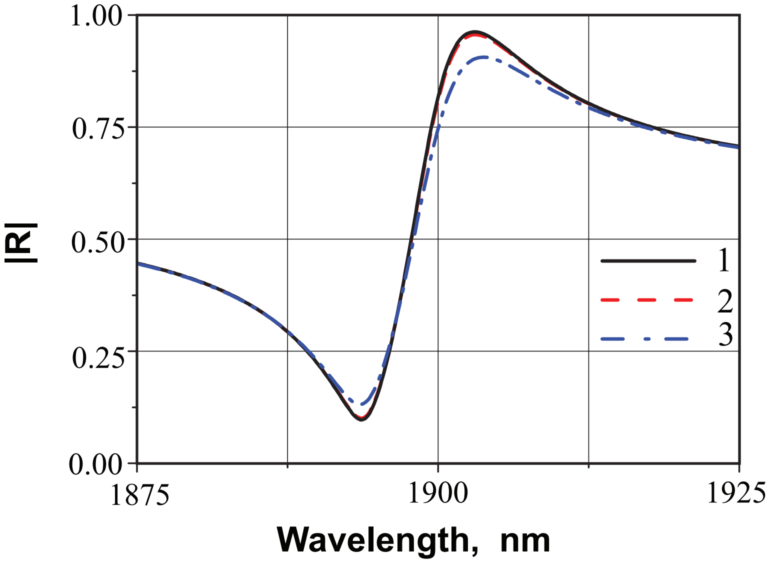


Figure 6. Wavelength dependences of reflection coefficient magnitude of two-element array made of germanium bars with taking into account germanium dissipation. The structure sizes are $d_x = d_y = 975$ nm, $l = 195$ nm, $h_1 = 877$ nm and $h_2 = 780$ nm. It is assumed that refractive index of germanium is 4.12 and dielectric loss tangent has values $\tan(\delta) = 0$ (line 1), $\tan(\delta) = 10^{-4}$ (line 2), and $\tan(\delta) = 10^{-3}$ (line 3).

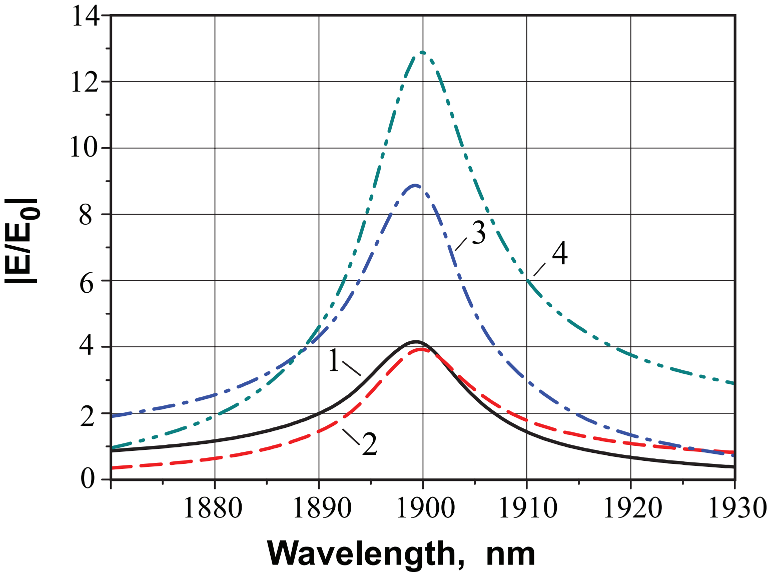


Figure 7. Wavelength dependences of ratio $|E|/|E_0|$ for some points within two-element array of germanium bars. The structure sizes are $d_x = d_y = 975$ nm, $l = 195$ nm, $h_1 = 877$ nm and $h_2 = 780$ nm. Refractive index of germanium is assumed to be 4.12. Lines 1 and 2 correspond to the center of shorter and longer bars, respectively. Lines 3 and 4 correspond to the center of air gaps between two adjacent shorter and longer bars, respectively.

light may be achieved in very thin structures. For both these possible applications an important question is how strong field intensity will be confined inside the structure and which form does wavelength dependence of this intensity have? It is evident that the Q-factor shows a field strengthening in the array.

The wavelength dependences of ratio $|E|/|E_0|$ are depicted in Fig. 7. Here $|E|$ is maximum of absolute value of electric field in one or another chosen point within array and $|E_0|$ is maximum of absolute value of electric field of incident wave in free space. The wavelength dependences of $|E|/|E_0|$ are shown in four different points. Lines 1 and 2 correspond to the center of the shorter and longer dielectric bars, respectively. Nearly these points the electric field reaches its maximum level in the dielectric bars. Lines 3 and 4 correspond to the center of air gaps between two adjacent shorter and longer bars, respectively. It should be noticed that the magnitude of electric field reaches its minima for both mentioned air gaps in these points (see Fig. 4,a). Magnitude of electric field enlarges more then 28 times in the centre of air gap between dielectric bars despite the fact that the electric field has a minimum value in referenced points. Maximum of the electric field magnitude in array corresponds to the wavelength 1899 nm. This wavelength is approximately equal to the central wavelength of trapped mode resonance ($(\lambda_1 + \lambda_2)/2 = 1898$ nm).

Increasing of Q-factor results in a rise of electric field intensity in the structure. For example, the maximum of ratio $|E|/|E_0|$ is 2.3 times more in the case of germanium array with $h_1 = 877$ nm and $h_2 = 838$ nm than in the case of array with $h_1 = 877$ nm and $h_2 = 780$ nm.

4. Conclusions

The problem of near infrared light reflection from and transmission through a planar 2-D dielectric arrays with a square periodic cell which consists of two dielectric bars with different lengths has been solved.

For the fist time the trapped mode resonance existence has been revealed in purely dielectric structures.

The clear-cut important distinction of dielectric array structures and metallic plasmonic ones is in the fact that dielectric arrays have essentially lower dissipation losses in visible and near infrared wavelength. Thus the proposed trapped mode dielectric arrays are promising to design very thin open planar structures with high quality factor and strong confinement field in array. They open new way for creating dielectric analog of lasing spacer and devices controlling light with light.

In contrast with arrays which bear plasmonic trapped mode, the resonance which appears in dielectric structure manifests a giant red shift relatively to wavelength of ordinary dimensional resonance of array with single dielectric bar in periodic cell. This remarkable property of purely dielectric trapped-mode arrays is important for possible applications in the promising field of infrared metamaterials. In particular, it gives us the way to design trapped mode structures by using materials with relatively small refractive index, for example, semiconductors.

Acknowledgments

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